

	1910	"semiconductor energy laboratory"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:01
	1910	"semiconductor energy laboratory"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:01
	53714	barrier adj layer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:02
	65	"semiconductor energy laboratory" and (barrier adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:24
	3430	crystallization and (tft or thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:26
	318636	nickel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:26
	1134	(crystallization and (tft or thin adj film adj transistor)) and nickel	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:27
	6040	gettering	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:27
	369	((crystallization and (tft or thin adj film adj transistor)) and nickel) and gettering	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:27
	91222	silicon adj nitride	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:28
	333	((crystallization and (tft or thin adj film adj transistor)) and nickel) and gettering) and (silicon adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:38
	5036	Joo.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:38
	47605	tft or thin adj film adj transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:39
	105	Joo.in. and (tft or thin adj film adj transistor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/02/08 16:39

	13	(metal adj mask) and "t-shaped" and (co or cobalt or ta or tantalum)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB USPAT	2003/02/11 11:11
	2	"t-shaped" adj etching adj mask	USPAT	2003/07/18 10:26
	1	"5452164".PN.	USPAT	2003/07/18 10:28
	1	6303392.URPN.	USPAT	2003/07/18 10:28
	9	("4814258" "4859573" "4988609" "5468595" "5658469" "5725997" "5885749" "6042975" "6303392").PN.	USPAT	2003/07/18 10:32